

### PHASE CONTROL THYRISTORS

- Junction Size: Square 250 mils
- Wafer Size: 4"
- $V_{RRM}$  Class: 1200 V
- Passivation Process: Glassivated MESA
- Reference IR Packaged Part: n. a.

### Major Ratings and Characteristics

Parameters	Units	Test Conditions
$V_{TM}$ Maximum On-state Voltage	1.3 V	$T_J = 25^\circ\text{C}$ , $I_T = 25\text{ A}$
$V_{RRM}$ Reverse Breakdown Voltage	1200 V	$T_J = 25^\circ\text{C}$ , $I_{RRM} = 100\ \mu\text{A}$ (1)
$I_{GT}$ Max. Required DC Gate Current to Trigger	100 mA	$T_J = 25^\circ\text{C}$ , anode supply = 6 V, resistive load
$V_{GT}$ Max. Required DC Gate Voltage to Trigger	2 V	$T_J = 25^\circ\text{C}$ , anode supply = 6 V, resistive load
$I_H$ Holding Current Range	5 to 200 mA	Anode supply = 6 V, resistive load
$I_L$ Maximum Latching Current	400 mA	Anode supply = 6 V, resistive load

(1) Nitrogen flow on die edge.

### Mechanical Characteristics

Nominal Back Metal Composition, Thickness	Cr - Ni - Ag (1 KA - 4 KA - 6 KA)
Nominal Front Metal Composition, Thickness	Cr - Ni - Ag (1 KA - 4 KA - 6 KA)
Chip Dimensions	250x250 mils (see drawing)
Wafer Diameter	100 mm, with std. <110> flat
Wafer Thickness	370 $\mu\text{m} \pm 10\ \mu\text{m}$
Maximum Width of Sawing Line	130 $\mu\text{m}$
Reject Ink Dot Size	0.25 mm diameter minimum
Ink Dot Location	See drawing
Recommended Storage Environment	Storage in original container, in dessicated nitrogen, with no contamination

# IR250SG12HCB

Bulletin I0210J 12/98

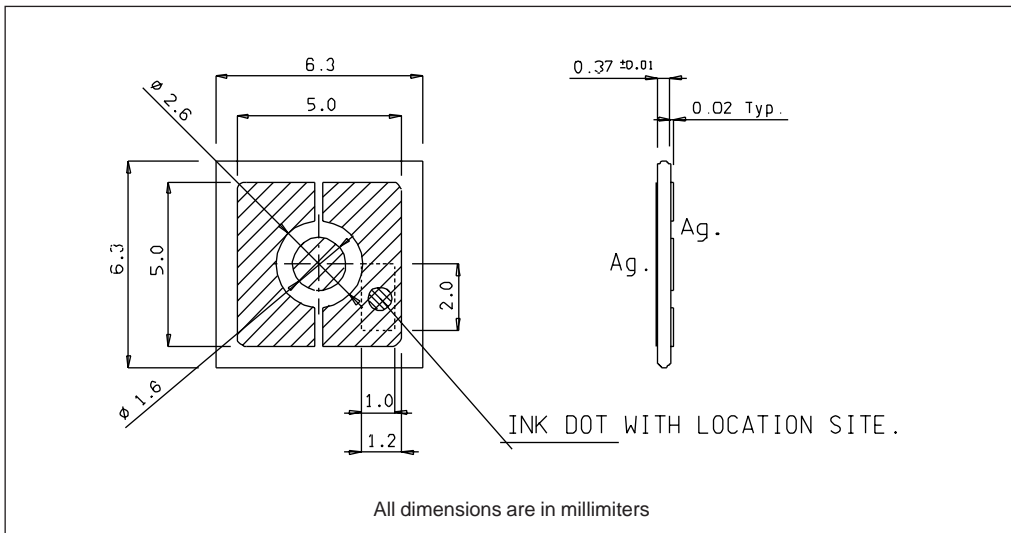
International  
**IR** Rectifier

## Ordering Information Table

Device Code						
IR	250	S	G	12	H	CB
1	2	3	4	5	6	7

- 1** - International Rectifier Device
- 2** - Chip Dimension in Mils
- 3** - Type of Device: S = Solderable SCR
- 4** - Passivation Process: G = Glassivated MESA
- 5** - Voltage code: Code x 100 =  $V_{RRM}$
- 6** - Metallization: H = Silver (Anode) - Silver (Cathode)
- 7** - CB = Probed Uncut Die (wafer in box)  
None = Probed Die in chip carrier

## Outline Table



## Wafer Layout

